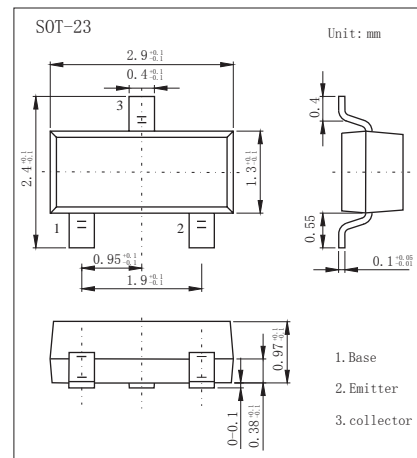


## PNP Transistors

### 2KB4001

#### ■ Features

- Collector Current:  $I_C = -1.5A$



#### ■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	-40	V
Collector-Emitter Voltage	$V_{CE0}$	-25	V
Emitter-Base Voltage	$V_{EB0}$	-5	V
Collector Current -Continuous	$I_C$	-1.5	A
Collector Power Dissipation	$P_C$	0.3	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to 150	$^\circ C$

#### ■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CB0}$	$I_C = -100 \mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{CE0}$	$I_C = -1mA, I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{EB0}$	$I_E = -100 \mu A, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -40V, I_E = 0$			-0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE} = -20V, I_B = 0$			-1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$			-0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = -1V, I_C = -100mA$	200		350	
		$V_{CE} = -1V, I_C = -800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800mA, I_B = -80mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800mA, I_B = -80mA$			-1.2	V
Base-emitter on voltage	$V_{BE(on)}$	$I_C = -1V, V_{CE} = -10mA$			-1	V
output capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$			20	pF
Transition frequency	$f_T$	$V_{CE} = -10V, I_C = -50mA, f = 30MHz$	100			MHz

#### ■ Marking

Marking	2D
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# 2KB4001

## Typical Characteristics

